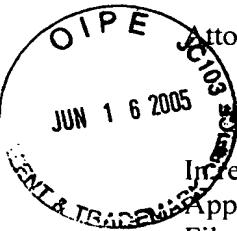


IFW
PATENT



Attorney Docket No.: 5308-389

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler
Application No.: 10/772,882
Filed: February 5, 2004

For: **NITRIDE HETEROJUNCTION TRANSISTORS HAVING CHARGE-TRANSFER INDUCED ENERGY BARRIERS AND METHODS OF FABRICATING THE SAME**

Confirmation No.: 8522
Group Art Unit: 2815
Examiner Name: Jerome Jackson, Jr.

Date: June 14, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004. Also enclosed is a translation or a concise explanation of each non-English language document enclosed. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

A handwritten signature of Elizabeth A. Stanek.

Elizabeth A. Stanek
Registration No. 48,568

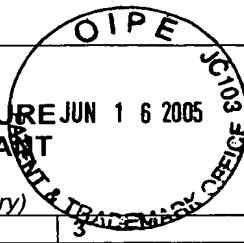
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Raleigh, North Carolina 27627
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CERTIFICATE OF MAILING UNDER 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 14, 2005.

A handwritten signature of Erin A. Campion.

Erin A. Campion



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**INFORMATION DISCLOSURE JUN 16 2005
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U.S. PATENTS AND PATENT PUBLICATIONS

FOREIGN PATENT DOCUMENTS

OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	8.	✓ Ando et al., "10-W/mm AlGaN-GaN HFET With a Field Modulating Plate," <i>IEEE Electron Device Letters</i> , 24(5), pp. 289-291 (May 2003).	
	9.	✓ Chini et al., "Power and Linearity Characteristics of Field-Plated Recessed-Gate AlGaN-GaN HEMTs," <i>IEEE Electron Device Letters</i> , 25(5), pp. 229-231 (May 2004).	
	10.	Gaska et al., "Self-Heating in High-Power AlGaN/GaN HFET's," <i>IEEE Electron Device Letters</i> , 19(3), pp. 89-91 (March 1998).	
	11.	Hikita et al., "350V/150A AlGaN/GaN Power HFET on Silicon Substrate With Source-via Grounding (SVG) Structure," <i>Electron Devices Meeting, 2004</i> , pp. 803-806, IEDM Technical Digest. IEEE International (Dec. 2004).	
	12.	Kanaev et al., "Femtosecond and Ultraviolet Laser Irradiation of Graphitelike Hexagonal Boron Nitride," <i>Journal of Applied Physics</i> , 96(8), pp. 4483-4489 (Oct. 15, 2004).	
	13.	Kanamura et al., "A 100-W High-Gain AlGaN/GaN HEMT Power Amplifier on a Conductive N-SiC Substrate for Wireless Base Station Applications," <i>Electron Devices Meeting, 2004</i> , pp. 799-802, IEDM Technical Digest. IEEE International (Dec. 2004).	
	14.	Karmalkar et al., "Very High Voltage AlGaN/GaN High Electron Mobility Transistors Using a Field Plate Deposited on a Stepped Insulator," <i>Solid State Electronics</i> , Vol. 45, pp. 1645-52 (2001).	
	15.	Kashahara et al., "Ka-ban 2.3W Power AlGaN/GaN Heterojunction FET," <i>IEDM Technical Digest</i> , pp. 677-680 (2002).	
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Examiner Signature _____ Date Considered _____

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet 2 of 3

Complete if Known

Application Number	10/772,882
Filing Date	February 5, 2004
First Named Inventor	Saxler
Group Art Unit	2815
Examiner Name	Jerome Jackson, Jr.

Attorney Docket Number 5308-389

OTHER NON PATENT LITERATURE DOCUMENTS

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	17.	Manfra et al., "Electron Mobility Exceeding 160 000 cm ² /V s in AlGaN/GaN Heterostructures Grown by Molecular-beam Epitaxy," <i>Applied Physics Letters</i> , 85(22), pp. 5394-96 (Nov. 29, 2004).	
	18.	Manfra et al., "High Mobility AlGaN/GaN Heterostructures Grown by Plasma-assisted Molecular beam epitaxy on Semi-Insulating GaN Templates Prepared by Hydride Vapor Phase Epitaxy," <i>Journal of Applied Physics</i> , 92(1), pp. 338-345 (July 1, 2002).	
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	20.	Parikh et al., "Development of Gallium Nitride Epitaxy and Associated Material-Device Correlation for RF, Microwave and MM-wave Applications," Cree, Inc. (35 slides).	
	21.	Saxler et al., "III-Nitride Heterostructures on High-Purity Semi-Insulating 4H-SiC Substrates for High-Power RF Transistors," International Workshop on Nitride Semiconductors (July 19, 2004).	
	22.	"Thick AlN template on SiC substrate – Novel semi insulating substrate for GaN-based devices," © 2003 by TDI, Inc., http://www.tdi.com/products/AIN_SiCT.html .	
	23.	Tilak et al., "Influence of Barrier Thickness on the High-Power Performance of AlGaN/GaN HEMTs," <i>IEEE Electron Device Letters</i> , 22(11), pp. 504-506 (Nov. 2001).	
	24.	United States Patent Application entitled "Improved Dielectric Passivation for Semiconductor Devices," Serial No. 10/851,507, filed May 22, 2004 (Cree Docket No. P0274).	
	25.	United States Patent Application entitled "Silicon Carbide on Diamond Substrates and Related Devices and Methods," Serial No. 10/707,898, filed January 22, 2004 (Cree Docket No. P0387).	
	26.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors with a Cap Layer and a Recessed Gate," Serial No. 10/897,726, filed July 23, 2004 (Attorney Docket No. 5308-392).	
	27.	United States Patent Application entitled "High Power Density and/or Linearity Transistors," Serial No. 11/005,107, filed December 6, 2004 (Attorney Docket No. 5308-511).	
	28.	United States Patent Application entitled "Field Effect Transistors (FETs) Having Multi-Watt Output Power at Millimeter-Wave Frequencies," Serial No. 11/005,423, filed December 6, 2004 (Attorney Docket No. 5308-512).	
	29.	United States Patent Application entitled "Group III Nitride Field Effect Transistors (FETs) Capable of Withstanding High Temperature Reverse Bias Test Conditions," Serial No. 11/080,905, filed March 15, 2005 (Attorney Docket No. 5308-516).	
	30.	United States Patent Application entitled "Aluminum Free Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,575, filed April 29, 2005 (Attorney Docket No. 5308-543).	
	31.	United States Patent Application entitled "Binary Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,675, filed April 29, 2005 (Attorney Docket No. 5308-544).	
	32.	United States Patent Application entitled "Composite Substrates of Conductive And Insulating or Semi-Insulating Group III-Nitrides For Group III-Nitride Devices," Serial No. 11/103,127, filed April 11, 2005 (Attorney Docket No. 5308-551).	
	33.	United States Patent Application entitled "Thick Semi-Insulating or Insulating Epitaxial Gallium Nitride Layers and Devices Incorporating Same," Serial No. 11/103,117, filed April 11, 2005 (Attorney Docket No. 5308-553).	
	34.	United States Patent Application entitled "Cap Layers and/or Passivation Layers for Nitride-Based Transistors, Transistor Structures and Methods of Fabricating Same," Serial No. 10/996,249, filed November 23, 2004 (Attorney Docket No. 5308-373).	
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	39.	Wu et al., "Bias-dependent Performance of High-Power AlGaN/GaN HEMTs," <i>IEDM Technical Digest</i> , p. 378-380 (2001).	

Examiner Signature

Date Considered

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				First Named Inventor	Saxler
				Group Art Unit	2815
				Examiner Name	Jerome Jackson, Jr.
Sheet	3	of	3	Attorney Docket Number	5308-389

OTHER NON PATENT LITERATURE DOCUMENTS				
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	40.	Wu et al., "Linearity Performance of GaN HEMTs With Field Plates," DRC 2004, Cree, Inc.		T
	41.	Wu et al., "Linearity Performance of GaN HEMTs With Field Plates," Cree Santa Barbara Technology Center, Goleta, CA 93117.		
	42.	Yu et al., "Schottky Barrier Engineering in III-V Nitrides via the Piezoelectric Effect," <i>Applied Physics Letters</i> , 73(13), pp. 1880-1882 (Sept. 28, 1998).		
	43.	Zhang et al., "High Breakdown GaN HEMT with Overlapping Gate Structure," <i>IEEE Electron Device Letters</i> , 21(9), pp. 421-423 (September 2000).		

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